ABSTRACT

DEEP SILICON ETCHING DEVICE AND GAS INTAKE SYSTEM FOR DEEP SILICON ETCHING DEVICE

A deep silicon etching device includes a reaction chamber, a gas source cabinet, and the gas source cabinet is connected with the reaction chamber through two independently controlled gas paths. Wherein, the first gas path is used for leading the process gas for etching into the reaction chamber from the gas source cabinet. The second gas path is used for leading the process gas for depositing into the reaction chamber from the gas source cabinet. The mixture and delay problem of the process gas in the switching of the steps can be solved by this invention.

Fig. 3